



30V N-Channel Trench Power MOSFET

General Description

The SJM30ND060 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a wide variety of applications.

Features

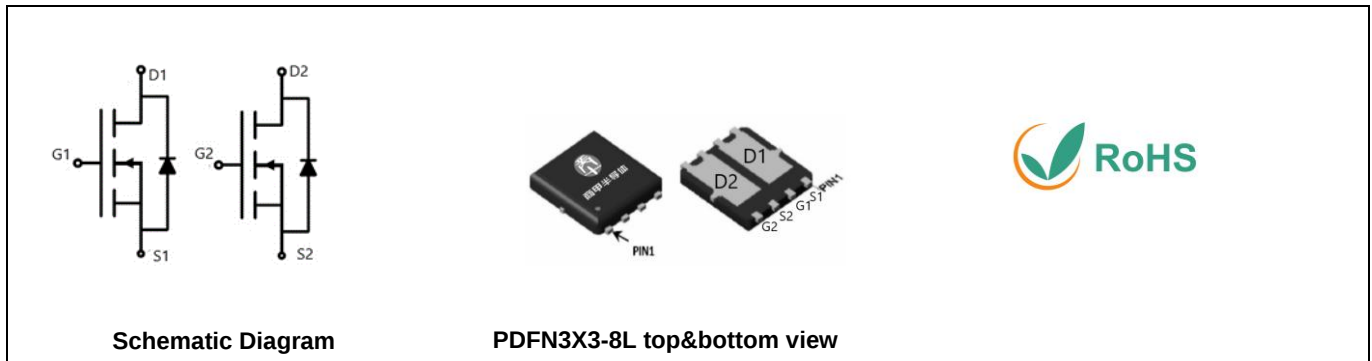
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

Application

- PWM Applications
- Load Switch
- Power Management

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(ON_TYP)}$	7.9	m Ω
I_D	44	A
Q_G	21.6	nC



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJM30ND060	SJM30ND060	PDFN3X3-8L	Tape	\	\	5000 Pcs

Table 1. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^{\circ}\text{C}$)	44	A
	Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	28	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	176	A
P_D	Maximum Power Dissipation($T_C=25^{\circ}\text{C}$)	30	W
	Maximum Power Dissipation($T_C=100^{\circ}\text{C}$)	12	W
E_{AS}	Avalanche energy (Note 2)	72	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		4.2	$^{\circ}\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =30V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1		2.5	V
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		25		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A T _J =25℃		7.9	9.9	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =10A T _J =25℃		11.3	14.7	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		1062		pF
C _{oss}	Output Capacitance			130		pF
C _{rss}	Reverse Transfer Capacitance			114		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		1.53		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		6.4		nS
t _r	Turn-on Rise Time			346		nS
t _{d(off)}	Turn-Off Delay Time			19.4		nS
t _f	Turn-Off Fall Time			9.8		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		21.2		nC
Q _{gs}	Gate-Source Charge			2.32		nC
Q _{gd}	Gate-Drain Charge			4.24		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				44	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =20A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, dI/dt=500A/μs		20		ns
Q _{rr}	Reverse Recovery Charge	I _F =20A, dI/dt=500A/μs		11		nC

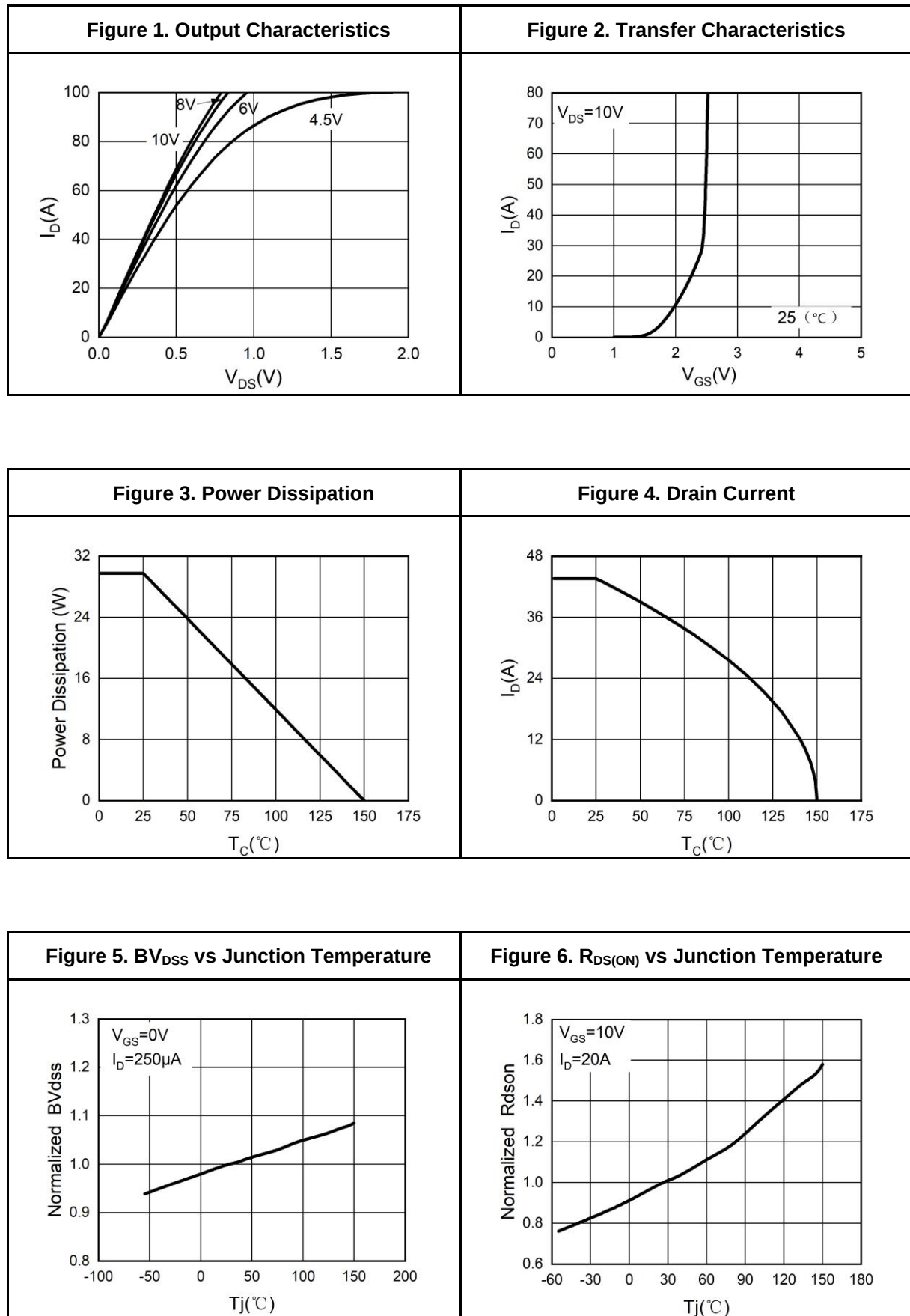
Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



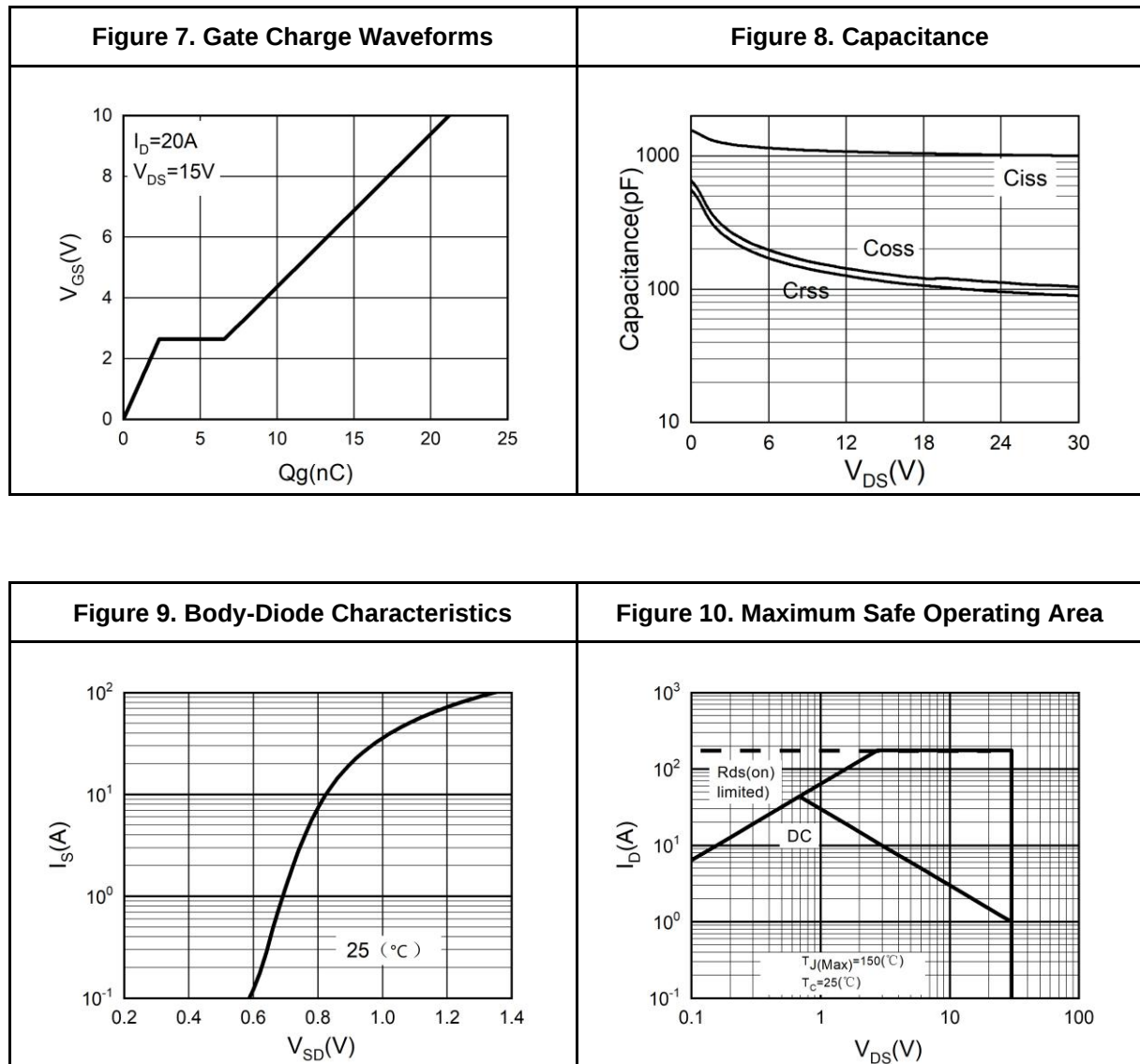
Typical Electrical And Thermal Characteristics (Curves)





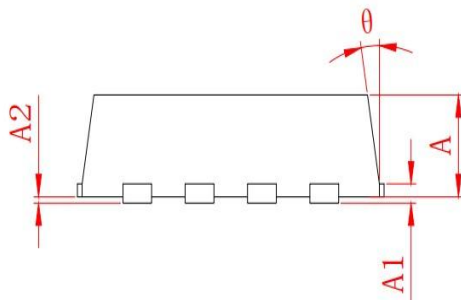
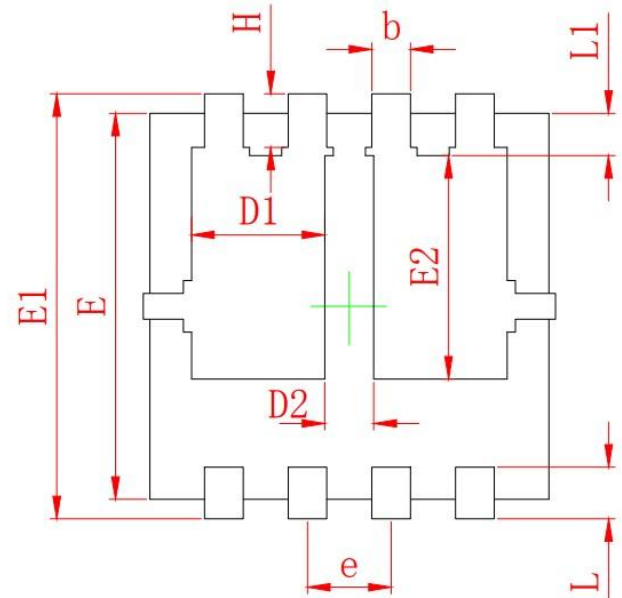
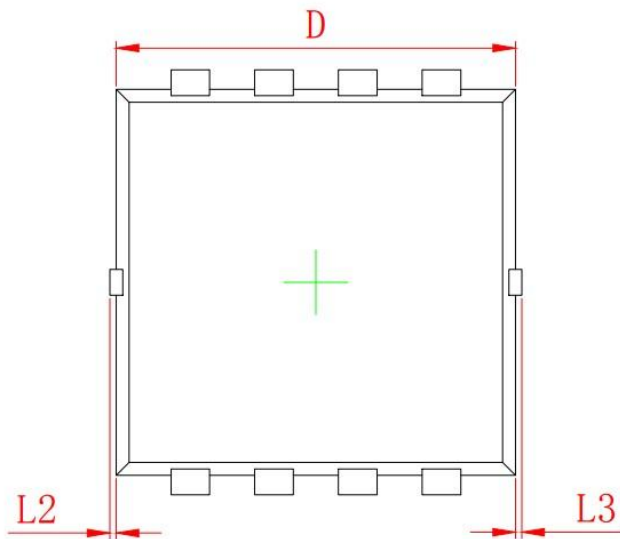
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Typical Electrical And Thermal Characteristics (Curves)





PDFN3X3-8L Package Information



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.700	0.900
A1	0.152 REF.	
A2	0~0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0~0.100	
L3	0~0.100	
H	0.315	0.515
θ	8°	12°



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